BC847CDXV6T1, BC847CDXV6T5 BC848CDXV6T1, BC848CDXV6T5



NPN Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-563 which is designed for low power surface mount applications.

Features

• These are Pb-Free Devices

MAXIMUM RATINGS

Rating	Symbol	BC847	BC848	Unit
Collector – Emitter Voltage	V _{CEO}	45	30	V
Collector – Base Voltage	V _{CBO}	50	30	V
Emitter – Base Voltage	V _{EBO}	6.0	5.0	V
Collector Current – Continuous	Ic	100	100	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

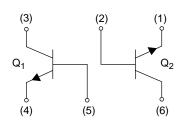
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) T _A = 25°C Derate above 25°C	P _D	357 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) T _A = 25°C	P _D	F00	>
Derate above 25°C		500 4.0	mW mW/°C
	R _{θJA}		

^{1.} FR-4 @ Minimum Pad



ON Semiconductor®

http://onsemi.com



BC847CDXV6T1



SOT-563 CASE 463A PLASTIC

MARKING DIAGRAMS



1x = Device Code

x = G or M

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC847CDXV6T1, BC847CDXV6T5 BC848CDXV6T1, BC848CDXV6T5

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	BC847CDXV6T1 BC848CDXV6T1	V _{(BR)CEO}	45 30	_ _	- -	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \mu A, V_{EB} = 0$)	BC847CDXV6T1 BC848CDXV6T1	V _{(BR)CES}	50 30	_ _	- -	V
Collector – Base Breakdown Voltage (I _C = 10 μA)	BC847CDXV6T1 BC848CDXV6T1	V _{(BR)CBO}	50 30	_ _	- -	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	BC847CDXV6T1 BC848CDXV6T1	V _{(BR)EBO}	6.0 5.0	_ _	-	V
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)		I _{CBO}	-	_ _	15 5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain $(I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V})$ $(I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V})$		h _{FE}	- 420	270 520	- 800	-
Collector – Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA)		V _{CE(sat)}	_ _	_ _	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)		V _{BE(sat)}	_ _	0.7 0.9	_ _	V
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)	V _{BE(on)}	580 -	660 -	700 770	mV	
SMALL-SIGNAL CHARACTERISTICS				•		
Current-Gain - Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	_	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	_	-	4.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 k Ω ,f = 1.0 kHz, BV	V = 200 Hz)	NF	_	-	10	dB

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]
BC847CDXV6T1		SOT-563	4000 Units / Tape & Reel
BC847CDXV6T1G		SOT-563 (Pb-Free)	4000 Units / Tape & Reel
BC847CDXV6T5	1G	SOT-563	8000 Units / Tape & Reel
BC847CDXV6T5G		SOT-563 (Pb-Free)	8000 Units / Tape & Reel
BC848CDXV6T1		SOT-563	4000 Units / Tape & Reel
BC848CDXV6T1G	1	SOT-563 (Pb-Free)	4000 Units / Tape & Reel
BC848CDXV6T5	1L	SOT-563	8000 Units / Tape & Reel
BC848CDXV6T5G		SOT-563 (Pb-Free)	8000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC847CDXV6T1, BC847CDXV6T5 BC848CDXV6T1, BC848CDXV6T5

TYPICAL CHARACTERISTICS

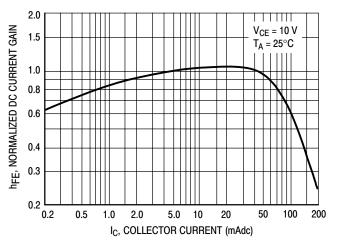


Figure 1. Normalized DC Current Gain

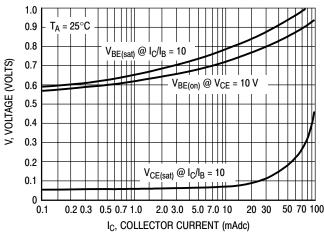


Figure 2. "Saturation" and "On" Voltages

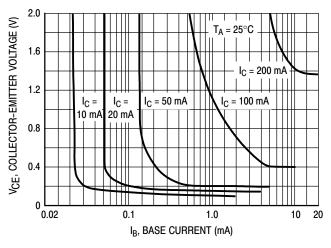


Figure 3. Collector Saturation Region

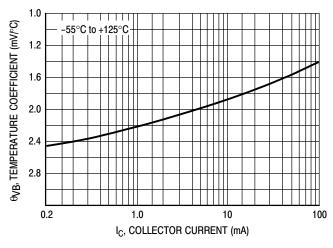


Figure 4. Base-Emitter Temperature Coefficient

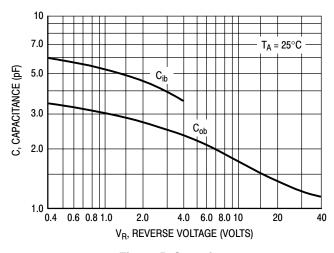


Figure 5. Capacitances

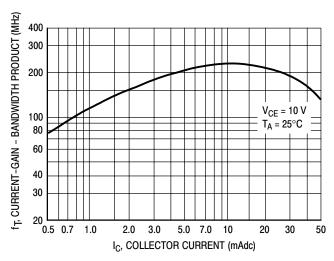
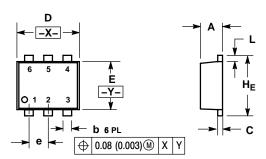


Figure 6. Current-Gain - Bandwidth Product

BC847CDXV6T1, BC847CDXV6T5 BC848CDXV6T1, BC848CDXV6T5

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01 ISSUE F



NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

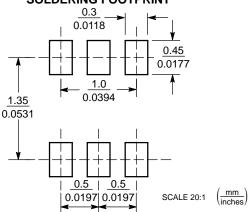
	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
Е	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC				0.02 BS0		
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

- STYLE 1: PIN 1. EMITTER 1

 - 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2

 - 5. BASE 2 6. COLLECTOR 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.